

FIGURE 1

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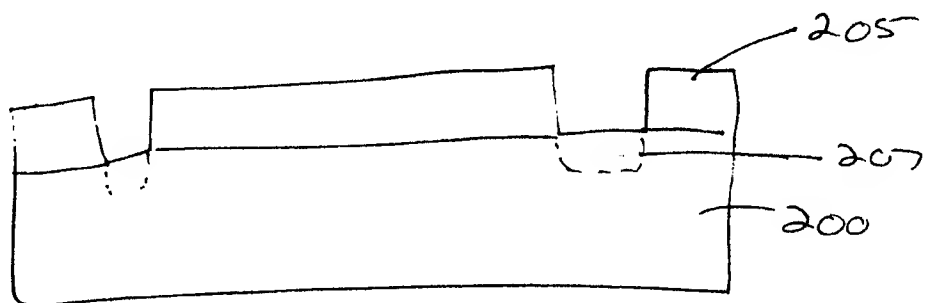


Fig 2(a)

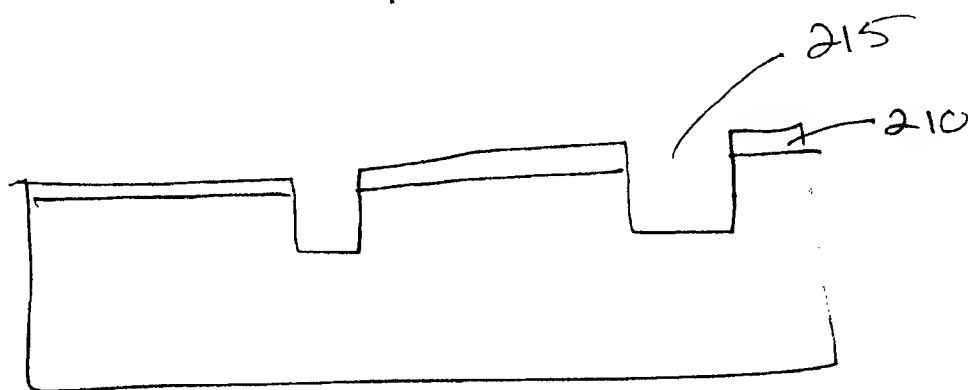


Fig 2(b)

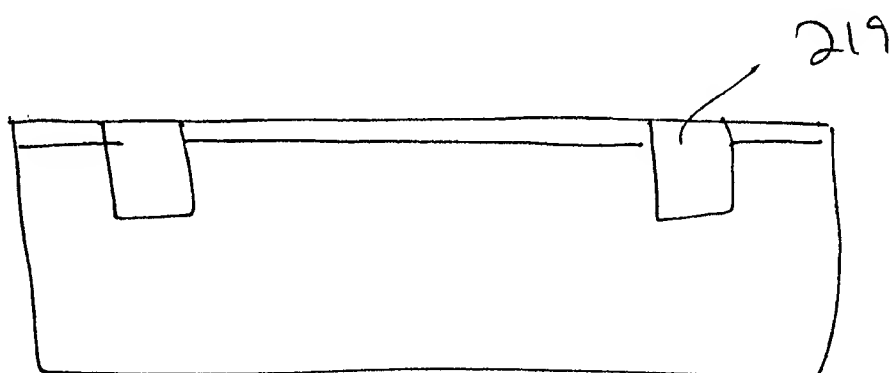


Fig 2(c)

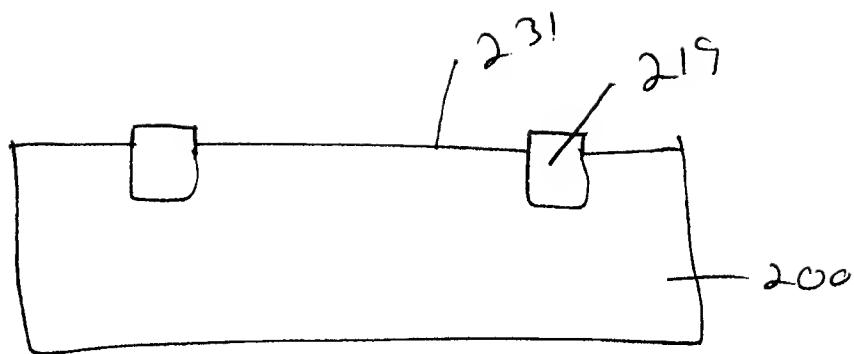


Fig 2(d)

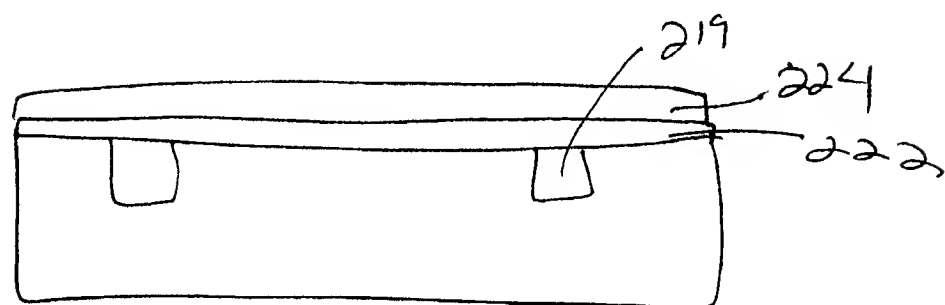


Fig 2(e)

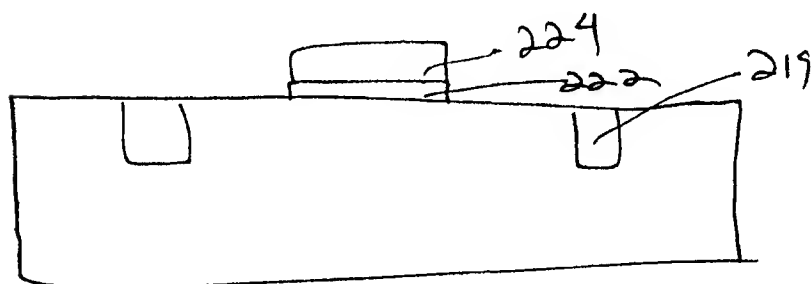


Fig 2(f)

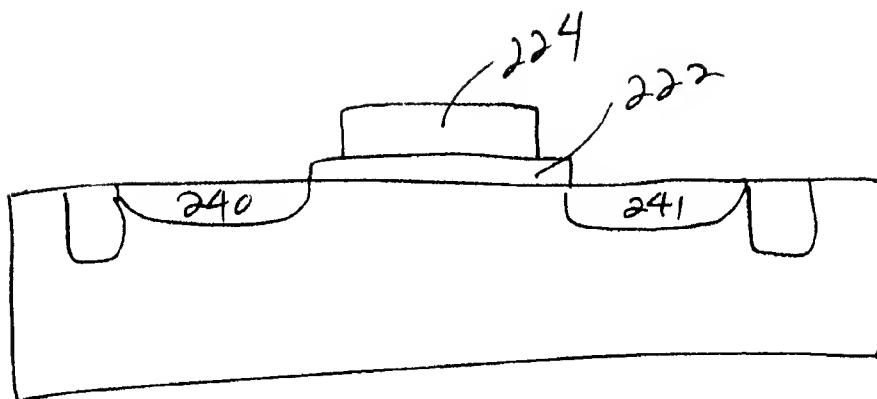


Fig. 2(g)

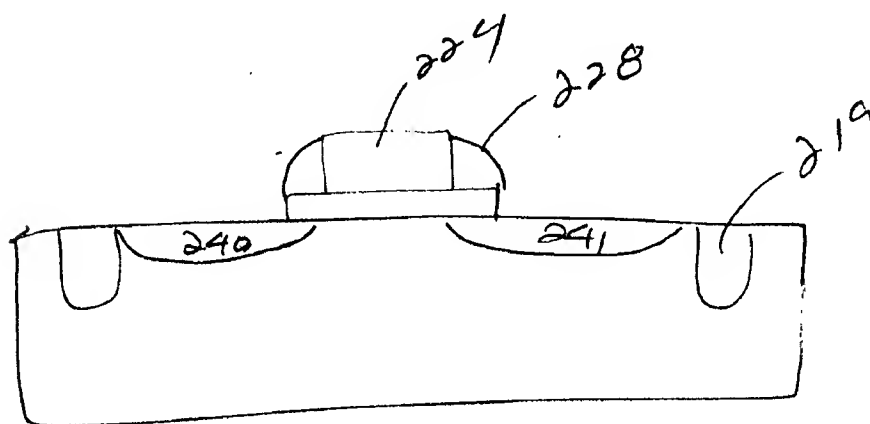


Fig 2(h)

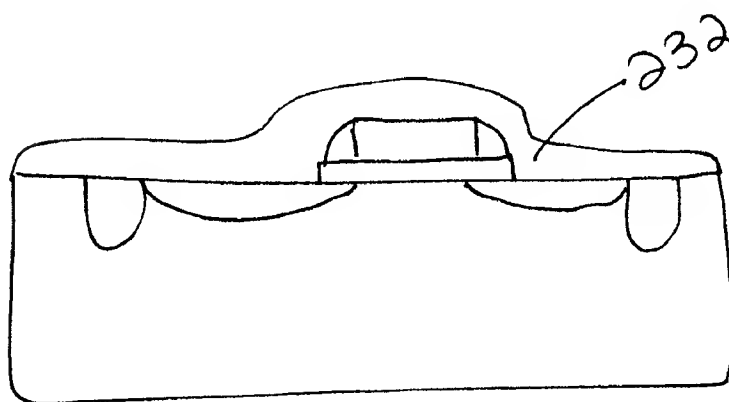


Fig 2(i)

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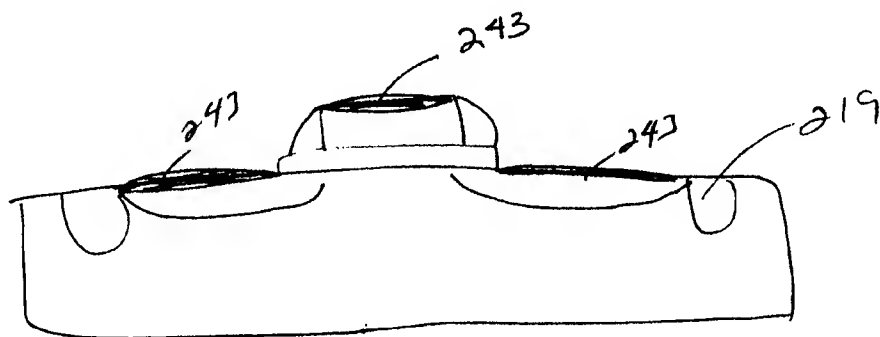


Fig 2(j)

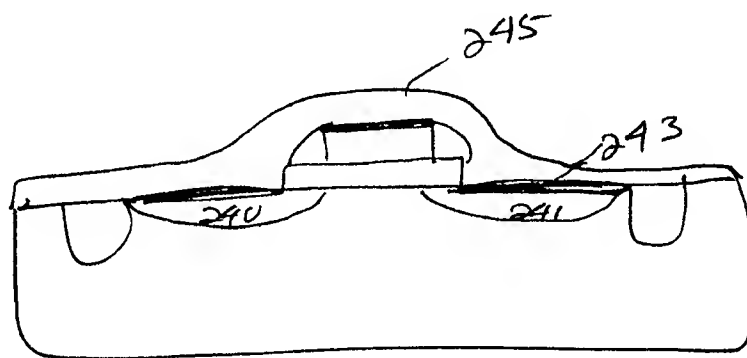


Fig 2(k)

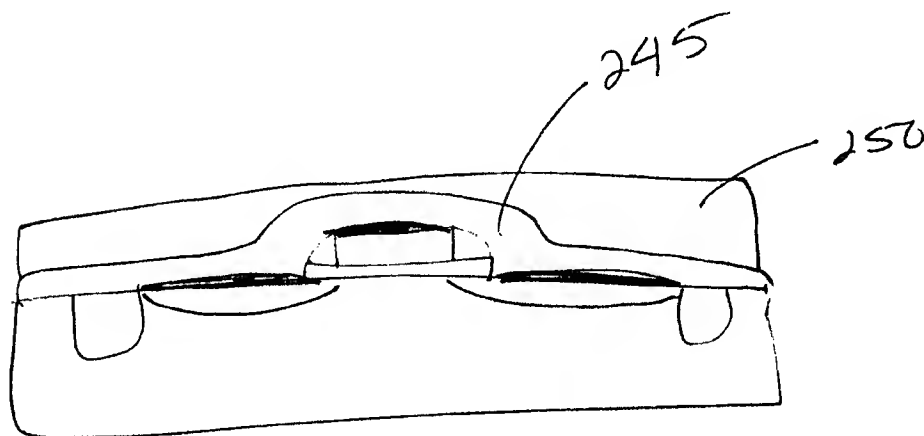


Fig 2(l)

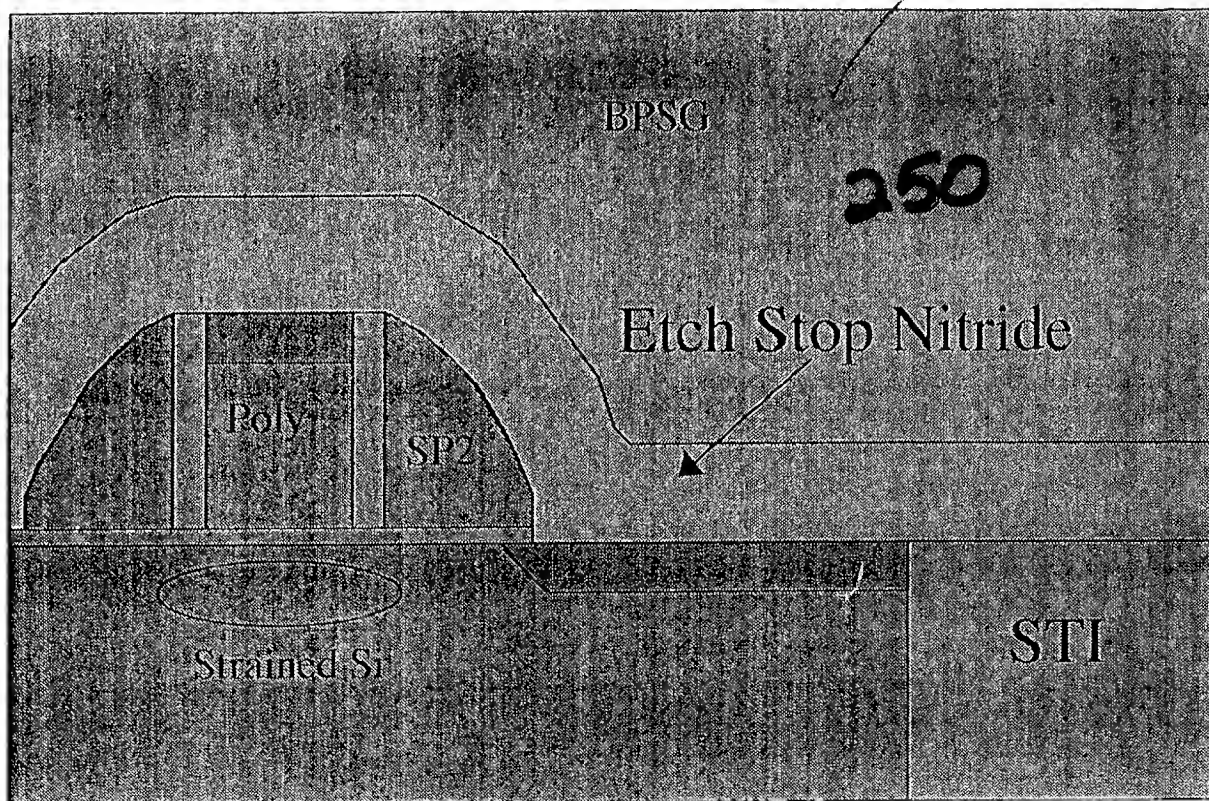


Fig.3

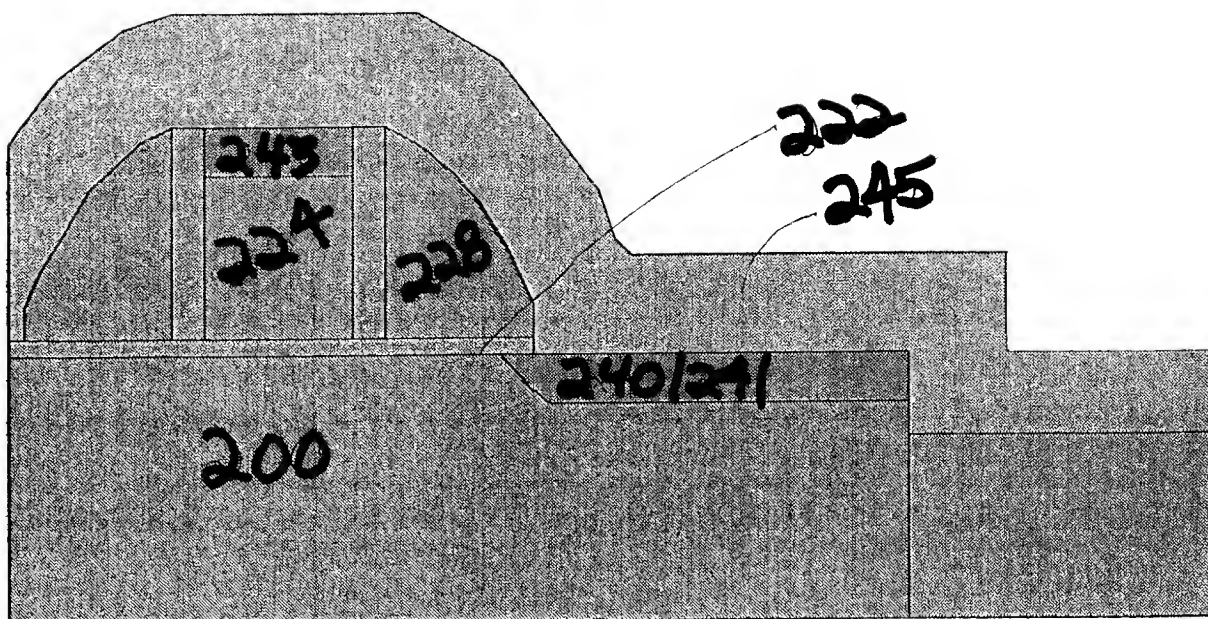


Fig.4

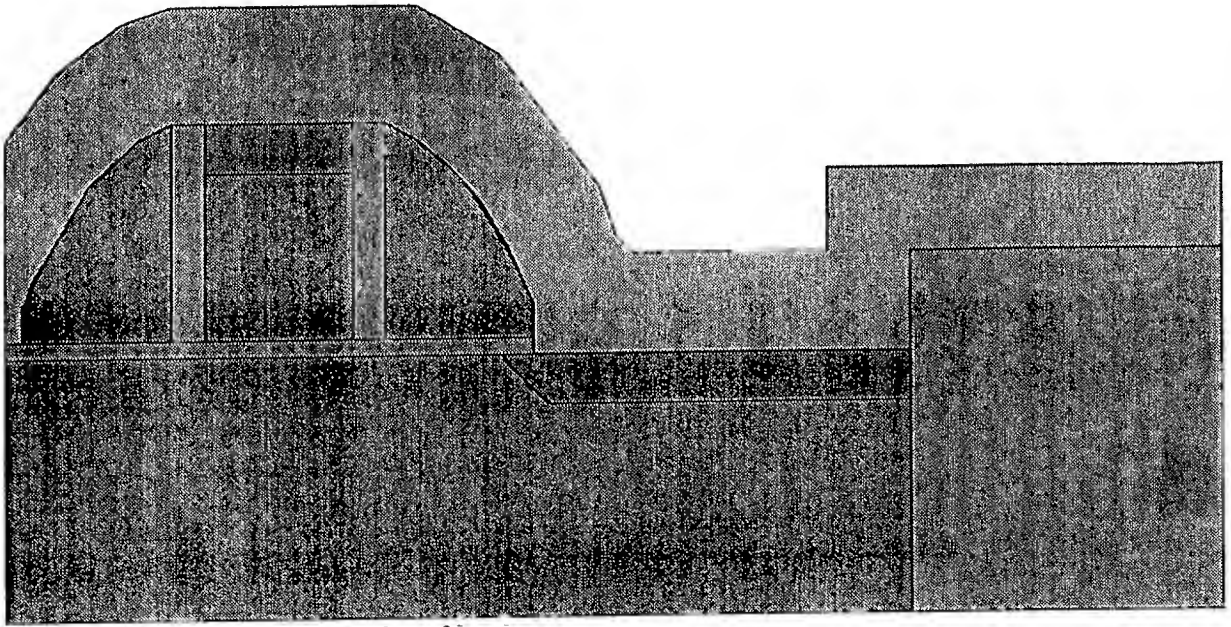


Fig 5

Stress Sxx vs. hight of STI-oxide
In Si cut at $y = +0.01\mu\text{m}$ and in film $y = -0.01\mu\text{m}$
Pressure (dynes/cm²)

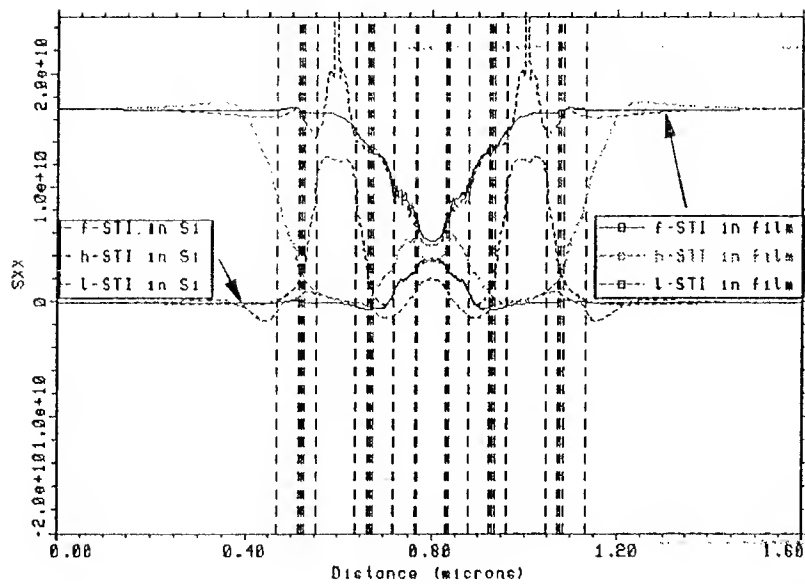


Fig.6

Stress Sxx vs. hight of STI-oxide
In Si cut at $y = +0.01\mu\text{m}$
Pressure (dynes/cm²)

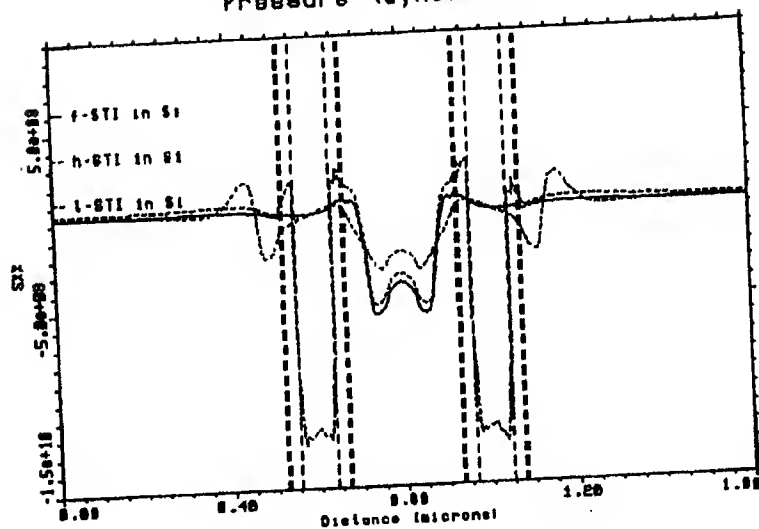


Fig. 7

Stress Sxx vs. hight of STI-oxide w/ large PC-STI distance
In Si cut at $y = -0.01\mu\text{m}$ and in film $y = 0.01\mu\text{m}$.
Pressure (dynes/cm²)

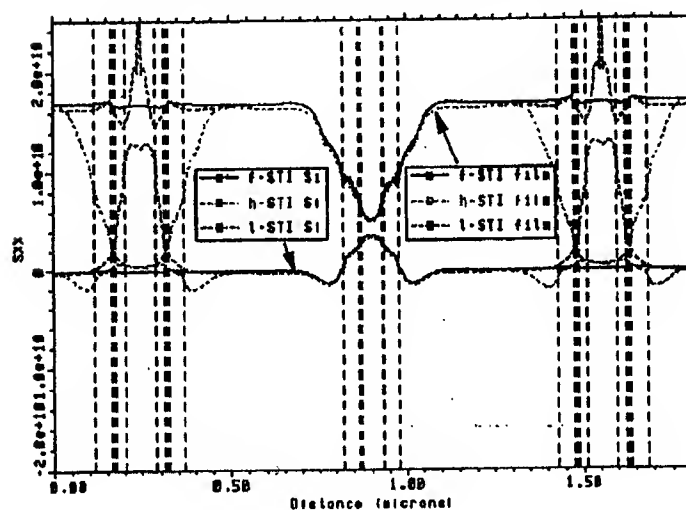


Fig. 8

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